PECVD-SiN standard recipe-1000A

1. Chamber Clean (wet clean)	**2. Chamber clean+coat**	**3.SiN Deposition**
WET CLEAN	**30CLN_SN**	**SiN_10**
Wipe clean upper chamber walls with DI	step1: Initial t=10", p=2x10-2 T=250C	step1: Initial t=10"
Wipe off upper chamber walls with IPA	step2: N_2 purge t=30" p=300mT	step2: N_2 purge t=30"
	step3: evacuate, base pressure=2x10-2, t=10"	step3: evacuate, t=10"
	step4:loop	step4:loop
	step5:gass stabilization, t=30"	step5: SiN gass stabilization, t=30"
	step6:etch chamber, t=30'	**step6:SiN deposition t=9'28.1"**
	step7:evacuate, t=10"	**Temperature=250°C**
	step8:N_2 purge	**Pressure=900mT**
	step9:evacuate	**Gass Flow:**
	step10:loop	**SiH_4=150sccm**
	step11:SiN gass stabilization	**N_2=450sccm**
	step12:SiN deposition(200A coat)	**NH_3=1.54sccm**
		Power:
		RF1=22W
	step13:evacuate	step7:evacuate, t=10"
	step14:N_2purge, t=30"	step8:N_2 purge t=30"
	step15:end	step9:evacuate t=10"
		step10:loop

Automatic - Process : _SIN10 Step: 6

Description: SiN Dep 1000 A
Process Pump: LOVAC
Deposition ID: SIN250
Deposition (Å): 1000

TEMPERATURE

	Setpt	Actual
Channel 2	250	248

	Setpt	Actual
Pressure(mTorr	900	903

GAS CHANNELS

	Setpt	Actual
SiH_4	150	149
N_2	450	450
NH_3	1.54	1.56

RF GENERATORS

RF1

RF Control: POWER
RF Config: PE

	Setpt	Actual
Power	22	21
Ref		0.0
DC		11

	Setpt	Elapsed	Left
Time	09:28.1	08:16.0	01:12.1